A 25 Watt, 5 GHz GaAs FET Amplifier for MLS

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A 25-Watt, 29-dB gain, 5-GHz FET amplifier for the transmitter in the Microwave Landing System has been developed using practical GaAs FETs assembled in ceramic packages with internal matching networks. This four-stage amplifier provides 30-Watt power output with 18.5% power efficiency at 17 dBm power input level.

❑ Return to main document.